P20B12SN

Power MOSFETs 120V, 20A, N-channel

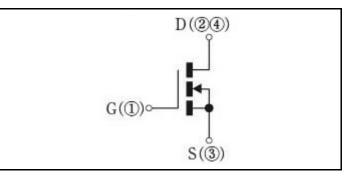
Feature

- N-channel
- SMD
- Low Ron
- 10V Gate Drive
- Low Capacitance
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel tempertature	Tch		-55 to 150	°C
Drain-source voltage	V _{DSS}		120	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		20	Α
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	60	А
Total power dissipation	P _T		44	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	18	А
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	37	mJ

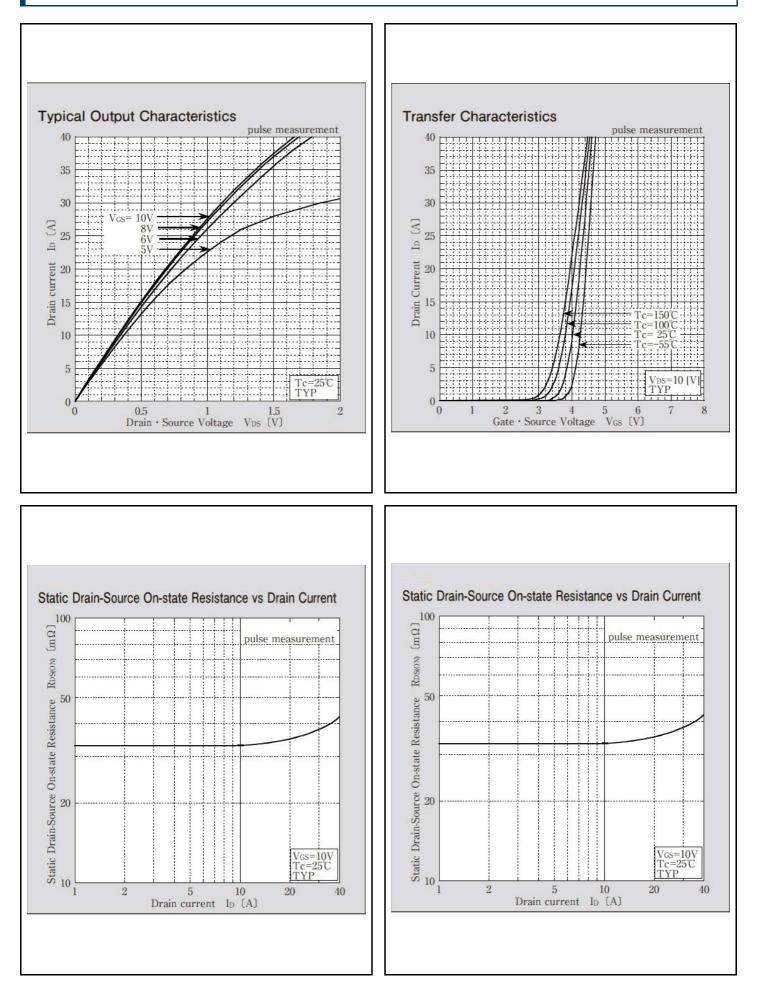
* : See the original Specifications

Electrical Characteristics	(unless otherwise specified : Tc=25°C)

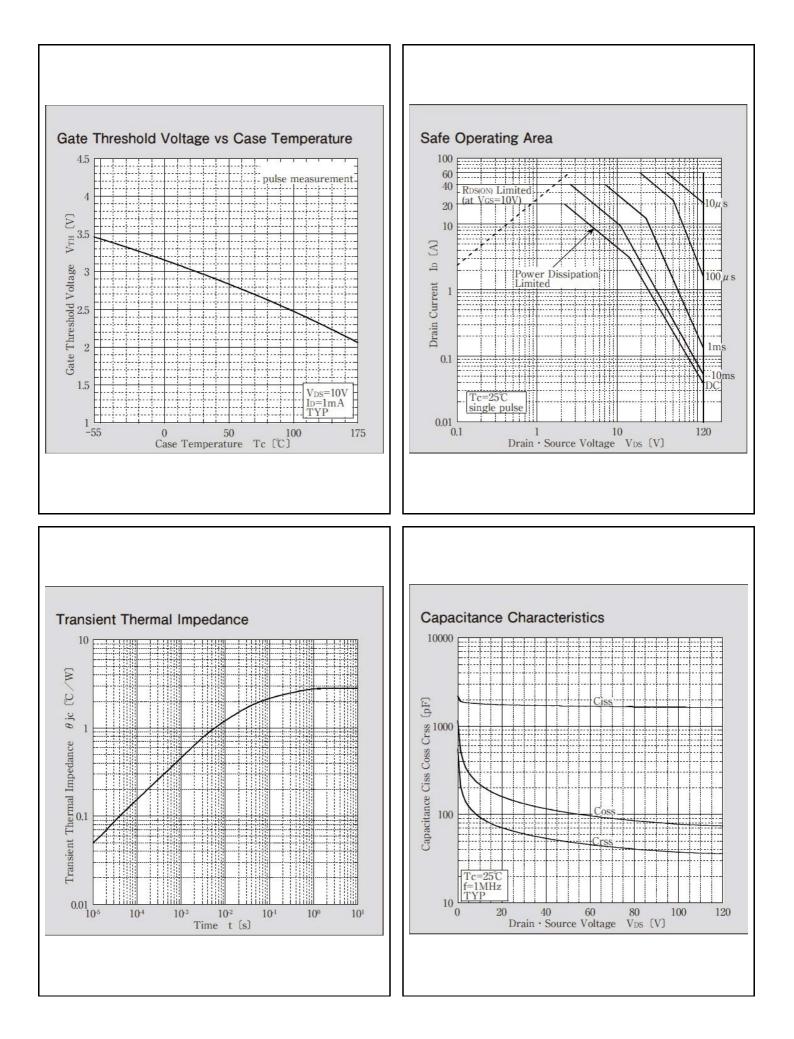
Item	Symbol	Conditions	Ratings			11
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	120			V
Zero gate voltage drain current	I _{DSS}	VDS=120V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g fs	ID=10A, VDS=10V	8	16		S
Static drain-source on-state resistance	R _{DS(ON)}	ID=10A, VGS=10V		0.033	0.042	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3	4	V
Source-drain diode forward voltage	V_{SD}	IS=20A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink *			2.84	°C/W
Total gate charge	Qg	VDD=96V, VGS=10V, ID=20A		37		nC
Gate to source charge	Qgs	VDD=96V, VGS=10V, ID=20A		12		nC
Gate to drain charge	Qgd	VDD=96V, VGS=10V, ID=20A		12		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		1740		рF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		65		рF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		144		pF
Turn-on delay time	td(on)	ID=10A, RL=6Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		7		ns
Rise time	tr	ID=10A, RL=6Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		10		ns
Turn-off delay time	td(off)	ID=10A, RL=6Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		22		ns
Fall time	tf	ID=10A, RL=6Ω, VDD=60V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		6		ns
Diode reverse recovery time	trr	IF=20A, VGS=0V, di/dt=100A/µs		59		ns
Diode reverse recovery charge	Qrr	IF=20A, VGS=0V, di/dt=100A/µs		128		nC

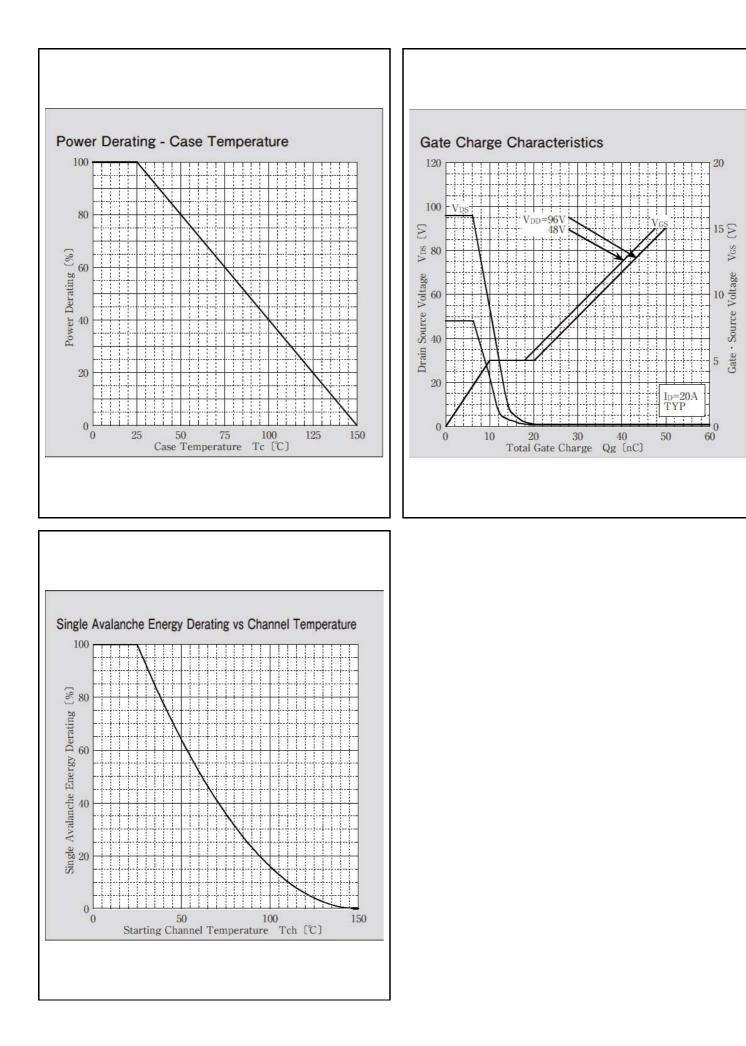
* : See the original Specifications

CHARACTERISTIC DIAGRAMS



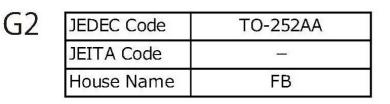
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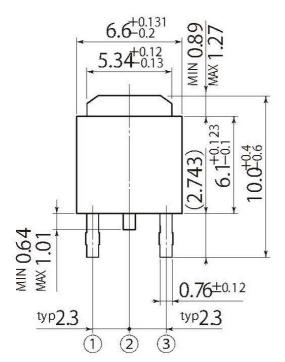


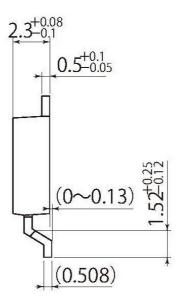


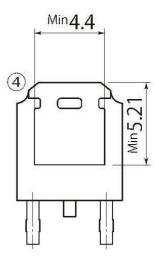
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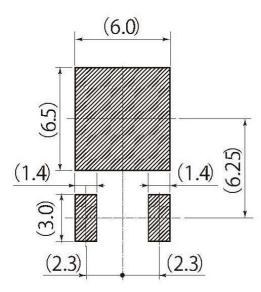
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Referential Soldering Pad

• Optimize soldering pad to the board design and soldering condition.

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